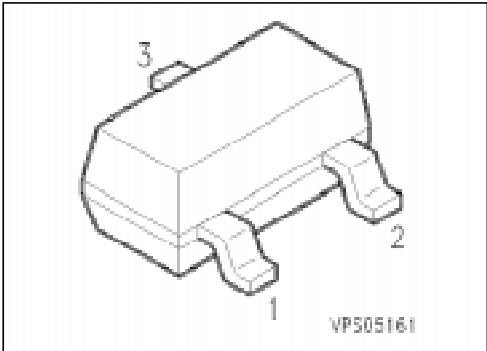


NPN Silicon RF Transistor

BF 799

- For linear broadband amplifier applications up to 500 MHz
- SAW filter driver in TV tuners



Type	Marking	Ordering Code (tape and reel)	Pin Configuration			Package ¹⁾
			1	2	3	
BF 799	LK	Q62702-F935	B	E	C	SOT-23

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE0}	20	V
Collector-emitter reverse voltage	V_{CES}	30	
Collector-base voltage	V_{CB0}	30	
Emitter-base voltage	V_{EB0}	3	
Collector current	I_C	35	mA
Peak collector current	I_{CM}	50	
Peak base current	I_{BM}	15	
Total power dissipation, $T_A \leq 25^\circ\text{C}$	P_{tot}	280	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	- 65 ... + 150	

Thermal Resistance

Junction - ambient ²⁾	$R_{th JA}$	≤ 450	K/W
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¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

Electrical Characteristics

at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

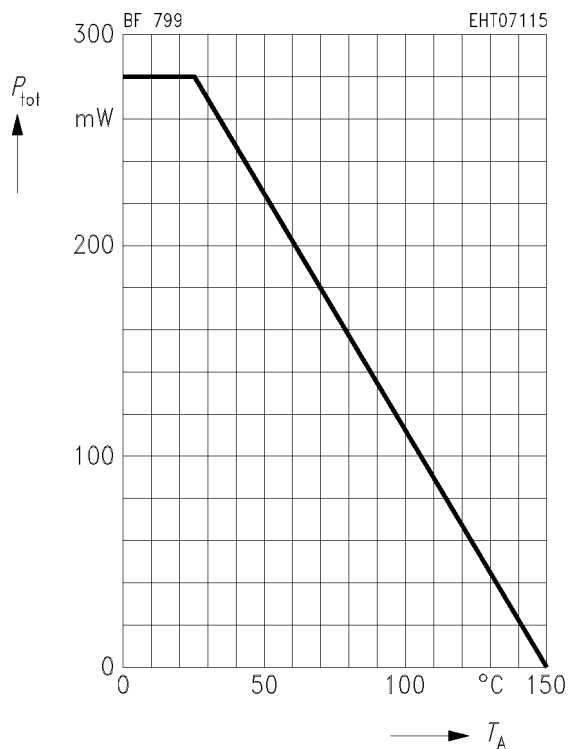
DC Characteristics

Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)\text{ CE0}}$	20	—	—	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$	$V_{(BR)\text{ CB0}}$	30	—	—	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)\text{ EB0}}$	3	—	—	
Collector cutoff current $V_{CB} = 20\text{ V}$	I_{CB0}	—	—	100	nA
DC current gain, $V_{CE} = 10\text{ V}$ $I_C = 5\text{ mA}$ $I_C = 20\text{ mA}$	h_{FE}	35 40	95 100	— 250	—
Collector-emitter saturation voltage $I_C = 20\text{ mA}$, $I_B = 2\text{ mA}$	$V_{CE\text{ sat}}$	—	0.15	0.5	V
Base-emitter saturation voltage $I_C = 20\text{ mA}$, $I_B = 2\text{ mA}$	$V_{BE\text{ sat}}$	—	—	0.95	

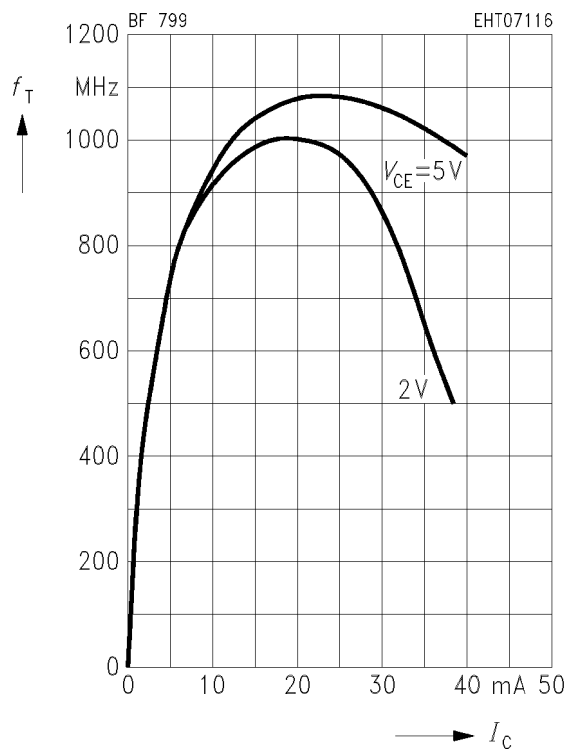
AC Characteristics

Transition frequency $I_C = 5\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 100\text{ MHz}$ $I_C = 20\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 100\text{ MHz}$	f_t	— —	800 1100	— —	MHz
Output capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $I_E = 0$	C_{ob}	—	0.96	—	pF
Collector-base capacitance $V_{CB} = 10\text{ V}$, $V_{BE} = 0\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	—	0.7	—	
Collector-emitter capacitance $V_{CE} = 10\text{ V}$, $V_{BE} = 0\text{ V}$, $f = 1\text{ MHz}$	C_{ce}	—	0.28	—	
Noise figure $I_C = 5\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 100\text{ MHz}$ $R_S = 50\text{ }\Omega$	F	—	3	—	dB
Output conductance $I_C = 20\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 35\text{ MHz}$	g_{22e}	—	60	—	μS

Total power dissipation $P_{\text{tot}} = f(T_A)$



Transition frequency $f_T = f(I_C)$ $f = 100 \text{ MHz}$



Collector-base capacitance $C_{cb} = f(V_{CB})$ $f = 1 \text{ MHz}$

